

# 74AHC595; 74AHCT595

8-bit serial-in/serial-out or parallel-out shift register with output latches; 3-state

Product data sheet

## 1. General description

The 74AHC595; 74AHCT595 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7A.

The 74AHC595; 74AHCT595 is an 8-stage serial shift register with a storage register and 3-state outputs. The shift register has separate clocks.

Data is shifted on the positive-going transitions of the shift register clock input (SHCP). The data in each register is transferred to the storage register on a positive-going transition of the storage register clock input (STCP). If both clocks are connected together, the shift register will always be one clock pulse ahead of the storage register.

The shift register has a serial input (DS) and a serial standard output (Q7S) for cascading. It is also provided with asynchronous reset (active LOW) for all 8 shift register stages. The storage register has 8 parallel 3-state bus driver outputs. Data in the storage register appears at the output whenever the output enable input ( $\overline{OE}$ ) is LOW.

## 2. Features

- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than  $V_{CC}$
- Input levels:
  - ◆ For 74AHC595: CMOS level
  - ◆ For 74AHCT595: TTL level
- ESD protection:
  - ◆ HBM EIA/JESD22-A114E exceeds 2000 V
  - ◆ MM EIA/JESD22-A115-A exceeds 200 V
  - ◆ CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

## 3. Applications

- Serial-to-parallel data conversion
- Remote control holding register



## 4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
<b>74AHC595</b>				
74AHC595D	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74AHC595PW	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74AHC595BQ	-40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1
<b>74AHCT595</b>				
74AHCT595D	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74AHCT595PW	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

## 5. Functional diagram

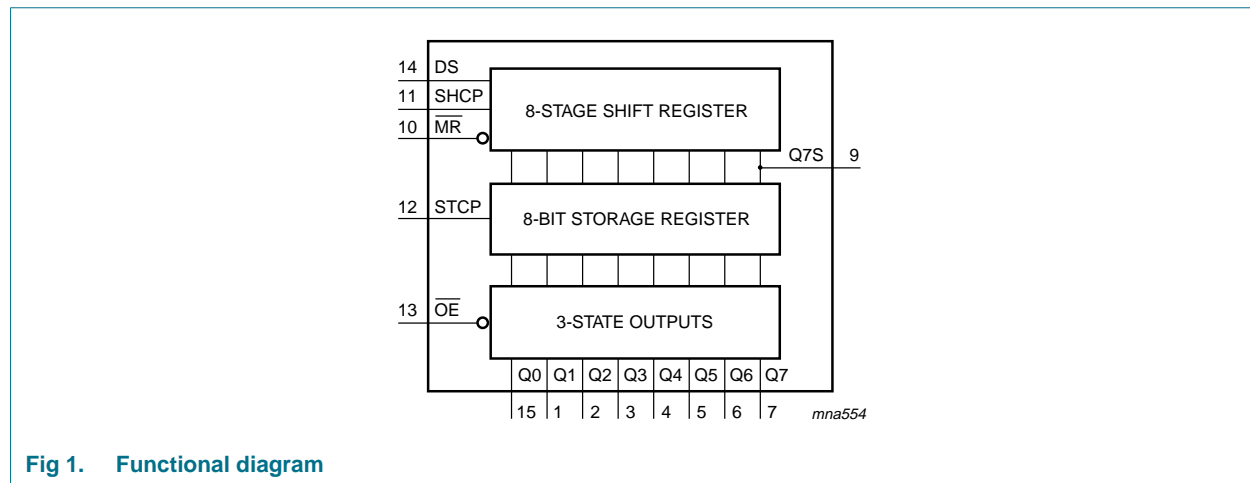


Fig 1. Functional diagram

## 8. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
$V_I$	input voltage		-0.5	+7.0	V
$I_{IK}$	input clamping current	$V_I < -0.5$ V	[1] -20	-	mA
$I_{OK}$	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1] -20	+20	mA
$I_O$	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5$ V)	-25	+25	mA
$I_{CC}$	supply current		-	+75	mA
$I_{GND}$	ground current		-75	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO16 packages: above 70 °C the value of  $P_{tot}$  derates linearly at 8 mW/K.

For TSSOP16 packages: above 60 °C the value of  $P_{tot}$  derates linearly at 5.5 mW/K.

For DHVQFN16 packages: above 60 °C the value of  $P_{tot}$  derates linearly at 4.5 mW/K.

## 9. Recommended operating conditions

**Table 5. Operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>74AHC595</b>						
$V_{CC}$	supply voltage		2.0	5.0	5.5	V
$V_I$	input voltage		0	-	5.5	V
$V_O$	output voltage		0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.0$ V to 3.6 V	-	-	100	ns/V
		$V_{CC} = 4.5$ V to 5.5 V	-	-	20	ns/V
<b>74AHCT595</b>						
$V_{CC}$	supply voltage		4.5	5.0	5.5	V
$V_I$	input voltage		0	-	5.5	V
$V_O$	output voltage		0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 4.5$ V to 5.5 V	-	-	20	ns/V

## 10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74AHC595</b>										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V <sub>CC</sub> = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V <sub>CC</sub> = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
I <sub>O</sub> = -8.0 mA; V <sub>CC</sub> = 4.5 V	3.94	-	-	3.80	-	3.70	-	V		
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
I <sub>O</sub> = 8.0 mA; V <sub>CC</sub> = 4.5 V	-	-	0.36	-	0.44	-	0.55	V		
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I <sub>OZ</sub>	OFF-state output current	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>O</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	±0.25	-	±2.5	-	±10	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	4.0	-	40	-	80	μA
C <sub>I</sub>	input capacitance		-	3	10	-	10	-	10	pF
<b>74AHCT595</b>										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -8.0 mA	3.94	-	-	3.80	-	3.70	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V

**Table 6. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
$I_I$	input leakage current	$V_I = 5.5 \text{ V}$ or GND; $V_{CC} = 0 \text{ V}$ to 5.5 V	-	-	0.1	-	1.0	-	2.0	$\mu\text{A}$
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND per input pin; other inputs at $V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 5.5 \text{ V}$	-	-	$\pm 0.25$	-	$\pm 2.5$	-	$\pm 10$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$ ; other inputs at $V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
$C_I$	input capacitance		-	3	10	-	10	-	10	pF

**Table 7. Dynamic characteristics ...continued**Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 13](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	Min	Max	
f <sub>max</sub>	maximum frequency	SHCP or STCP; see <a href="#">Figure 8</a> and <a href="#">9</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V	80	125	-	60	-	40	-	MHz
		V <sub>CC</sub> = 4.5 V to 5.5 V	130	170	-	110	-	90	-	MHz
t <sub>w</sub>	pulse width	SHCP HIGH or LOW; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V	5.0	-	-	5.0	-	5.0	-	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	5.0	-	-	5.0	-	5.0	-	ns
		STCP HIGH or LOW; see <a href="#">Figure 9</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V	5.0	-	-	5.0	-	5.0	-	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	5.0	-	-	5.0	-	5.0	-	ns
		MR LOW; see <a href="#">Figure 11</a>								
t <sub>su</sub>	set-up time	DS to SHCP; see <a href="#">Figure 9</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V	3.5	-	-	3.5	-	3.5	-	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	3.0	-	-	3.0	-	3.0	-	ns
		SHCP to STCP; see <a href="#">Figure 10</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V	8.5	-	-	8.5	-	8.5	-	ns
t <sub>h</sub>	hold time	DS to SHCP; see <a href="#">Figure 10</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.5	-	-	1.5	-	1.5	-	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	ns
t <sub>rec</sub>	recovery time	MR to SHCP; see <a href="#">Figure 11</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V	3.0	-	-	3.0	-	3.0	-	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	2.5	-	-	2.5	-	2.5	-	ns
C <sub>PD</sub>	power dissipation capacitance	f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub> <a href="#">[6]</a> <a href="#">[7]</a>	-	180	-	-	-	-	-	pF

**74AHCT595; V<sub>CC</sub> = 4.5 V to 5.5 V**

t <sub>pd</sub>	propagation delay	SHCP to Q7S; see <a href="#">Figure 8</a> <a href="#">[2]</a>								
		C <sub>L</sub> = 15 pF	-	3.8	8.2	1.0	9.0	1.0	10.0	ns
		C <sub>L</sub> = 50 pF	-	5.2	10.0	1.0	11.0	1.0	12.0	ns
		STCP to Qn; see <a href="#">Figure 9</a> <a href="#">[2]</a>								
		C <sub>L</sub> = 15 pF	-	4.0	7.4	1.0	8.5	1.0	9.5	ns
		C <sub>L</sub> = 50 pF	-	5.3	9.0	1.0	10.5	1.0	11.5	ns
		MR to Q7S; see <a href="#">Figure 11</a> <a href="#">[3]</a>								
		C <sub>L</sub> = 15 pF	-	4.6	8.2	1.0	9.5	1.0	10.5	ns
C <sub>L</sub> = 50 pF	-	5.8	10.5	1.0	11.5	1.0	12.5	ns		

**Table 7. Dynamic characteristics ...continued**Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 13](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	Min	Max	
t <sub>en</sub>	enable time	$\overline{OE}$ to Qn; see <a href="#">Figure 12</a> <sup>[4]</sup>								
		C <sub>L</sub> = 15 pF	-	4.8	9.0	1.0	11.0	1.0	12.0	ns
		C <sub>L</sub> = 50 pF	-	6.2	11.6	1.0	13.0	1.0	14.5	ns
t <sub>dis</sub>	disable time	$\overline{OE}$ to Qn; see <a href="#">Figure 12</a> <sup>[5]</sup>								
		C <sub>L</sub> = 15 pF	-	3.6	6.9	1.0	8.0	1.0	9.0	ns
		C <sub>L</sub> = 50 pF	-	5.8	10.3	1.0	11.0	1.0	12.0	ns
f <sub>max</sub>	maximum frequency	SHCP and STCP; see <a href="#">Figure 8</a> and <a href="#">9</a>	130	170	-	110	-	90	-	MHz
t <sub>w</sub>	pulse width	SHCP HIGH or LOW; see <a href="#">Figure 8</a>	5.0	-	-	5.0	-	5.0	-	ns
		STCP HIGH or LOW; see <a href="#">Figure 9</a>	5.0	-	-	5.0	-	5.0	-	ns
		$\overline{MR}$ LOW; see <a href="#">Figure 11</a>	5.0	-	-	5.0	-	5.0	-	ns
t <sub>su</sub>	set-up time	DS to SHCP; see <a href="#">Figure 9</a>	3.0	-	-	3.0	-	3.0	-	ns
		SHCP to STCP; see <a href="#">Figure 10</a>	5.0	-	-	5.0	-	5.0	-	ns
t <sub>h</sub>	hold time	DS to SHCP; see <a href="#">Figure 10</a>	2.0	-	-	2.0	-	2.0	-	ns
t <sub>rec</sub>	recovery time	$\overline{MR}$ to SHCP; see <a href="#">Figure 11</a>	3.0	-	-	3.0	-	3.0	-	ns
C <sub>PD</sub>	power dissipation capacitance	f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub> <sup>[6]</sup> <sup>[7]</sup>	-	190	-	-	-	-	-	pF

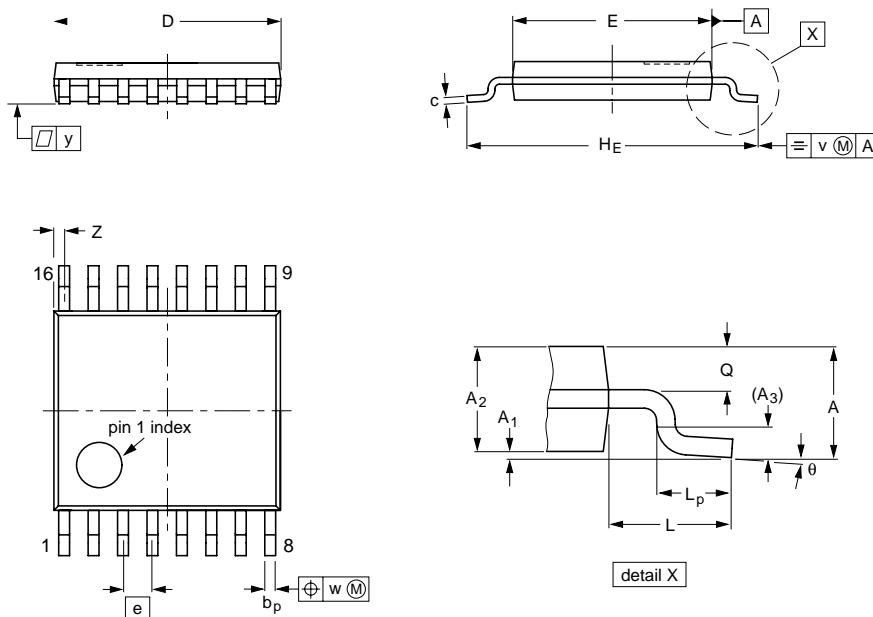
[1] Typical values are measured at nominal supply voltage.

[2] t<sub>pd</sub> is the same as t<sub>PHL</sub> and t<sub>PLH</sub>.[3] t<sub>pd</sub> is the same as t<sub>PHL</sub> only.[4] t<sub>en</sub> is the same as t<sub>PZL</sub> and t<sub>PZH</sub>.[5] t<sub>dis</sub> is the same as t<sub>PLZ</sub> and t<sub>PHZ</sub>.[6] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).P<sub>D</sub> = C<sub>PD</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>i</sub> + Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) where:f<sub>i</sub> = input frequency in MHz;f<sub>o</sub> = output frequency in MHz;Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of outputs;C<sub>L</sub> = output load capacitance in pF;V<sub>CC</sub> = supply voltage in V.

[7] All 9 outputs switching.

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



**DIMENSIONS (mm are the original dimensions)**

UNIT	A <sub>max.</sub>	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(2)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

**Notes**

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION
	IEC	JEDEC	JEITA	
SOT403-1		MO-153		

Fig 15. Package outline SOT403-1 (TSSOP16)